Claims:

1. A complementary MISFET comprising:

a first linear body including an N-type MISFET and a second linear body including a P-type MISFET; and

a separation region arranged between said first linear body and said second linear body.

2. The complementary MISFET of claim 1, wherein each cross section having a plurality of regions for forming said MISFET is continuously or intermittently formed in the longitudinal direction.

3. The complementary MISFET of claim 1 or 2, wherein said linear bodies and/or said separation region are formed of a material made of an organic semiconductor or electroconductive polymer.

4. An integrated circuit comprising the complementary MISFET of any one of claims 1 through 3.

5. A production method of the complementary MISFET of any one of claims 1 through 3, the method comprising the step of:

forming the separation region by coating or vapor depositing an insulating material between the plurality of linear bodies.

6. A production method of the complementary MISFET of any one of claims 1 through 3, the method comprising the step of:

forming an insulating film on a surface of the linear body to thereby form the separation region.

7. An integrated circuit comprising:

a plurality of linear bodies, each having a cross section which has a plurality of regions for forming a circuit element formed in said linear body and which is continuously or intermittently formed in the longitudinal direction.

8. The integrated circuit of claim 7, wherein said integrated circuit is a semiconductor memory, an image sensor, or a PLA.

9. The integrated circuit of claim 7 or 8, wherein said linear bodies are formed of a material made of an organic semiconductor or electroconductive polymer.

10. The integrated circuit of any one of claims 4 and 7 through 9, wherein said linear body has a cross section in a circular, polygonal, star, crescent, petal, character shape, or another arbitrary shape.